## NSN 5961-00-779-9139

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**Inclosure Material:** 

Metal all transistor

**Overall Length:** 

0.195 inches all transistor and 0.205 inches all transistor

**Terminal Length:** 

0.500 inches all transistor

**Overall Diameter:** 

0.205 inches all transistor and 0.215 inches all transistor

**Function For Which Designed:** 

Chopper

**Internal Configuration:** 

Junction contact all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-18 all transistor

**Electrode Internally-electrically Connected To Case:** 

Collector all transistor

**Internal Junction Configuration:** 

Npn all transistor

**Component Function Relationship:** 

Matched

**Component Name And Quantity:** 

2 transistor

**Mounting Method:** 

Terminal all transistor

**Terminal Circle Diameter:** 

0.090 inches all transistor and 0.110 inches all transistor

**Features Provided:** 

Hermetically sealed case

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

60.0 collector to base voltage, dc all transistor and 9.0 emitter to base voltage, dc all transistor and 10.0 emitter to collector voltage, dc all transistor and 45.0 collector-to-emitter, substaining voltage, base open-circuited all transistor

**Current Rating Per Characteristic:** 

100.00 milliamperes source cutoff current all transistor

**Power Rating Per Characteristic:** 

1.2 watts small-signal input power, common-collector absolute all transistor

**Maximum Operating Tempurature Per Measurement Point:** 

175.0 degrees celsius junction all transistor

**Terminal Type And Quantity:** 

3 uninsulated wire lead all transistor

Shelf Life:

N/a

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Demilitarization:

No

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